

isc N-Channel MOSFET Transistor

IRF740

DESCRIPTION

- Drain Current $-I_D = 10A @ T_C = 25^\circ C$
- Drain Source Voltage-
: $V_{DSS} = 400V (Min)$
- Static Drain-Source On-Resistance
: $R_{DS(on)} = 0.55 \Omega (Max)$
- Fast Switching Speed

APPLICATIONS

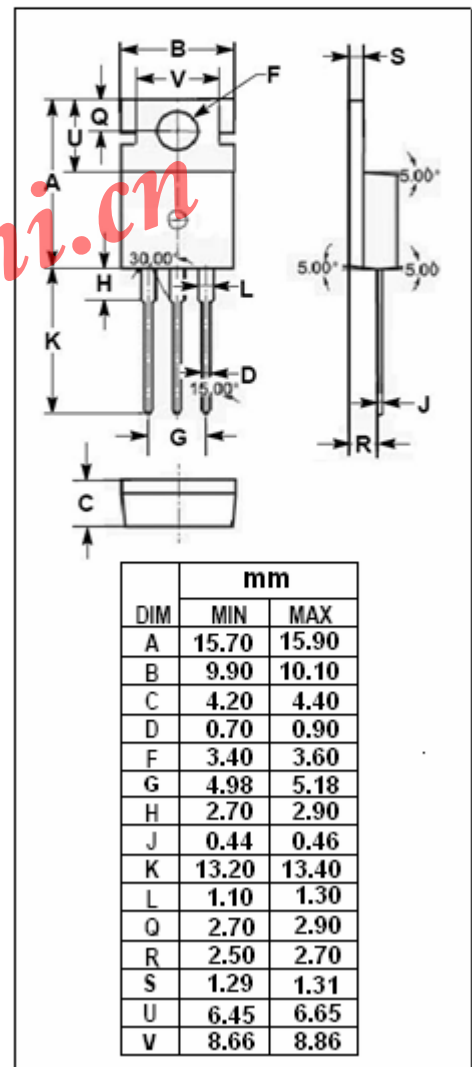
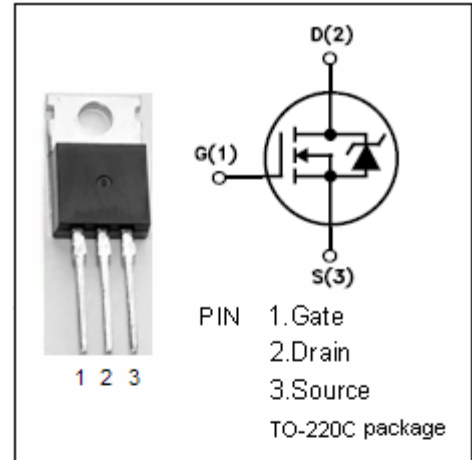
- Designed especially for high voltage, high speed applications, such as off-line switching power supplies, UPS, AC and DC motor controls, relay and solenoid drivers.

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS} = 0$)	400	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous @ $T_C = 25^\circ C$	10	A
P_{tot}	Total Dissipation @ $T_C = 25^\circ C$	125	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-65~150	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	1.0	$^\circ C/W$



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• ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0$; $I_D=0.25\text{mA}$	400		V
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$; $I_D=0.25\text{mA}$	2	4	V
$R_{DS(ON)}$	Drain-Source On-stage Resistance	$V_{GS}=10\text{V}$; $I_D=5\text{A}$		0.55	Ω
I_{GSS}	Gate Source Leakage Current	$V_{GS}=\pm 20\text{V}$; $V_{DS}=0$		± 500	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=400\text{V}$; $V_{GS}=0$		250	μA
V_{SD}	Diode Forward Voltage	$I_F=10\text{A}$; $V_{GS}=0$		2.2	V

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